

Static Characteristics
T_J = 25°C unless otherwise specified
APT19F100J

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(DSS)}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	1000			V
$\Delta V_{BR(DSS)}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, $I_D = 250\mu A$		1.15		V/°C
$R_{DS(on)}$	Drain-Source On Resistance ^③	$V_{GS} = 10V, I_D = 16A$		0.39	0.44	Ω
$V_{GS(th)}$	Gate-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5mA$	2.5	4	5	V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold Voltage Temperature Coefficient			-10		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1000V, T_J = 25°C$ $V_{GS} = 0V, T_J = 125°C$			250 1000	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS} = \pm 30V$			±100	nA

Dynamic Characteristics
T_J = 25°C unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
g_{fs}	Forward Transconductance	$V_{DS} = 50V, I_D = 16A$		34		S
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 25V$ $f = 1MHz$		8500		pF
C_{rss}	Reverse Transfer Capacitance			115		
C_{oss}	Output Capacitance			715		
$C_{o(cr)}^{④}$	Effective Output Capacitance, Charge Related	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 667V$		290		
$C_{o(er)}^{⑤}$	Effective Output Capacitance, Energy Related			150		
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 10V, I_D = 16A,$ $V_{DS} = 500V$		260		nC
Q_{gs}	Gate-Source Charge			46		
Q_{gd}	Gate-Drain Charge			125		
$t_{d(on)}$	Turn-On Delay Time	Resistive Switching $V_{DD} = 667V, I_D = 16A$ $R_G = 2.2\Omega^{⑥}, V_{GG} = 15V$		36		ns
t_r	Current Rise Time			37		
$t_{d(off)}$	Turn-Off Delay Time			140		
t_f	Current Fall Time			35		

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode (body diode)			20	A
I_{SM}	Pulsed Source Current (Body Diode) ^①				120	
V_{SD}	Diode Forward Voltage	$I_{SD} = 16A, T_J = 25°C, V_{GS} = 0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 16A^{③}$ $V_{DD} = 100V$ $di_{SD}/dt = 100A/\mu s$	$T_J = 25°C$		290	ns
			$T_J = 125°C$		600	
Q_{rr}	Reverse Recovery Charge		$T_J = 25°C$	1.3		μC
			$T_J = 125°C$	3.5		
I_{rrm}	Reverse Recovery Current		$T_J = 25°C$	10.6		A
			$T_J = 125°C$	14.2		
dv/dt	Peak Recovery dv/dt	$I_{SD} \leq 16A, di/dt \leq 1000A/\mu s, V_{DD} = 667V,$ $T_J = 125°C$			25	V/ns

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at $T_J = 25°C, L = 14.65mH, R_G = 2.2\Omega, I_{AS} = 16A$.

③ Pulse test: Pulse Width < 380μs, duty cycle < 2%.

④ $C_{o(cr)}$ is defined as a fixed capacitance with the same stored charge as C_{OSS} with $V_{DS} = 67\%$ of $V_{(BR)DSS}$.

⑤ $C_{o(er)}$ is defined as a fixed capacitance with the same stored energy as C_{OSS} with $V_{DS} = 67\%$ of $V_{(BR)DSS}$. To calculate $C_{o(er)}$ for any value of V_{DS} less than $V_{(BR)DSS}$, use this equation: $C_{o(er)} = -2.47E-7/V_{DS}^2 + 4.36E-8/V_{DS} + 8.44E-11$.

⑥ R_G is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

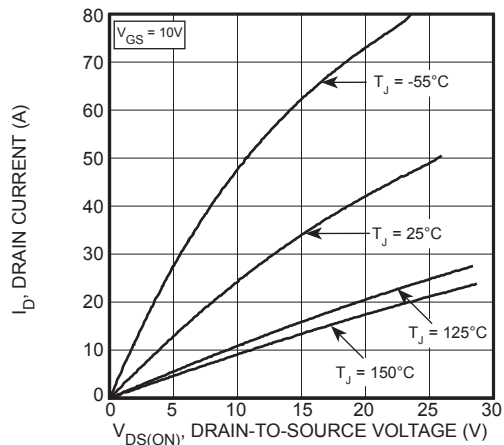


Figure 1, Output Characteristics

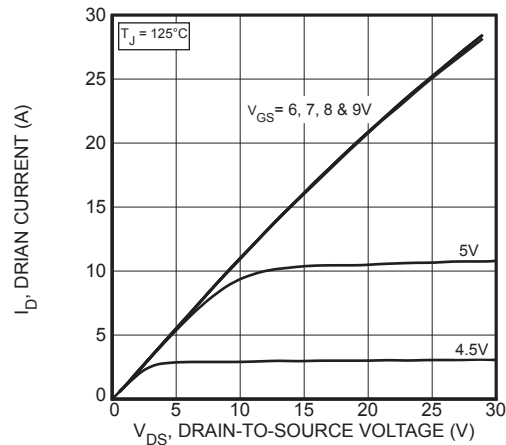


Figure 2, Output Characteristics

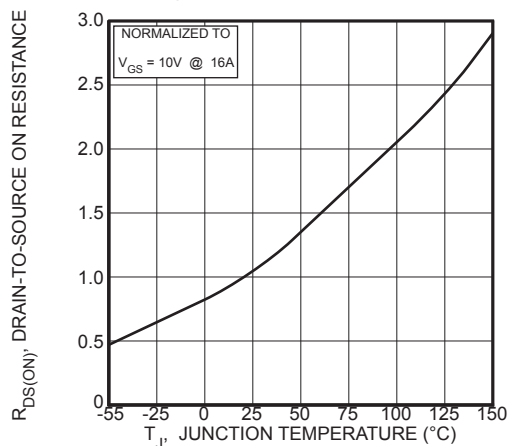
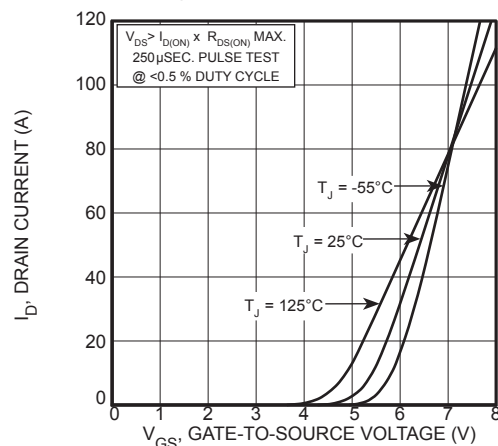
Figure 3, $R_{DS(ON)}$ vs Junction Temperature

Figure 4, Transfer Characteristics

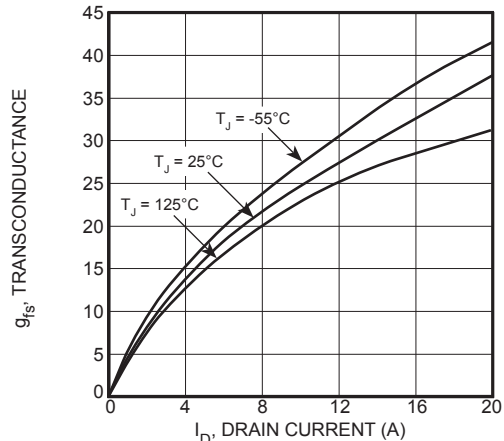


Figure 5, Gain vs Drain Current

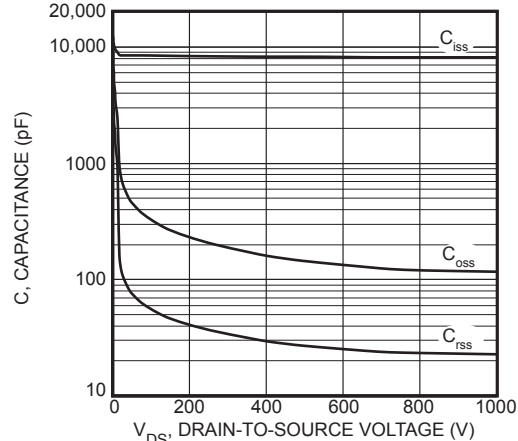


Figure 6, Capacitance vs Drain-to-Source Voltage

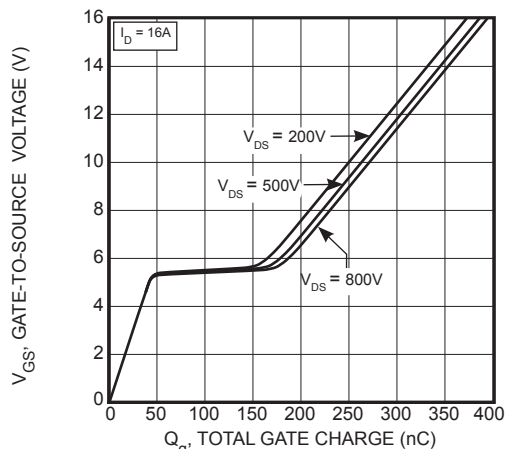


Figure 7, Gate Charge vs Gate-to-Source Voltage

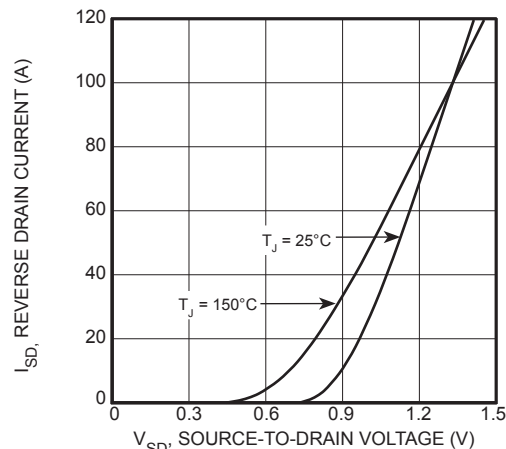


Figure 8, Reverse Drain Current vs Source-to-Drain Voltage

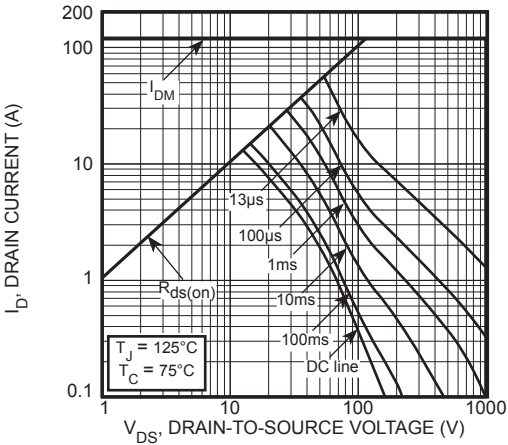


Figure 9, Forward Safe Operating Area

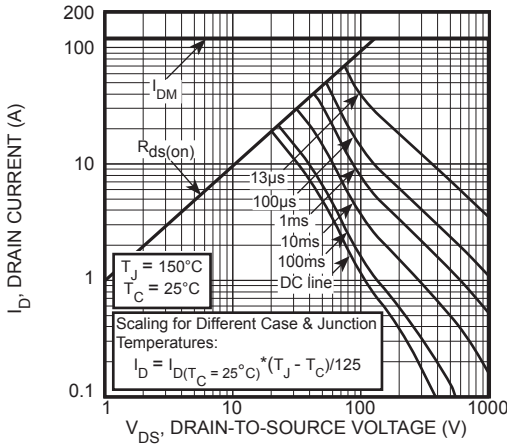


Figure 10, Maximum Forward Safe Operating Area

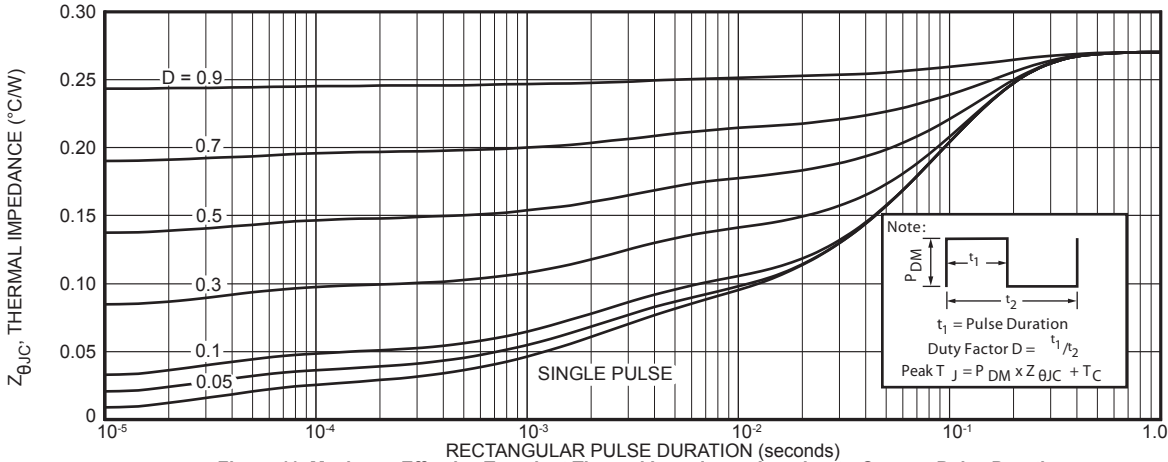
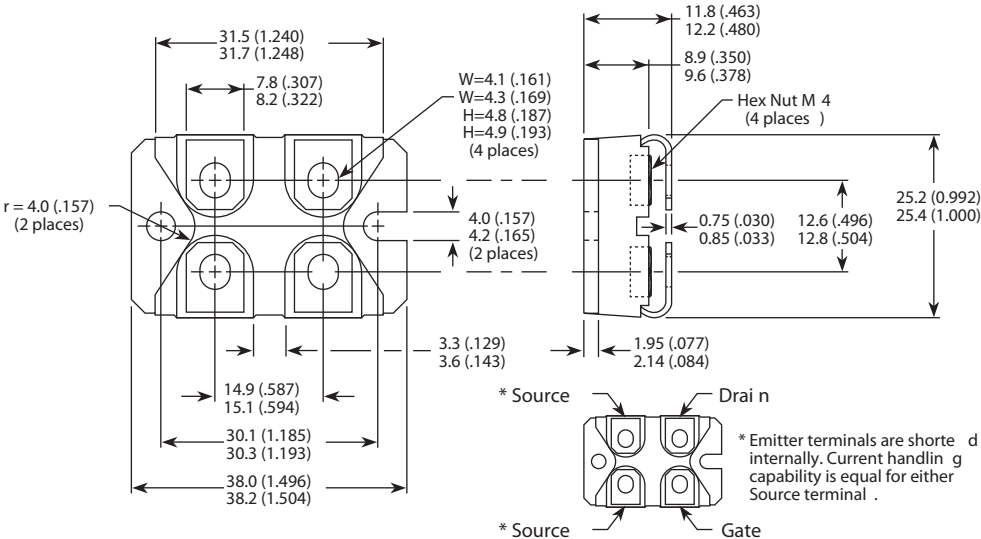


Figure 11. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)